Supporting Information

# Fabry-Pérot interference enhanced GaSe Visible-blind UV Photodetectors

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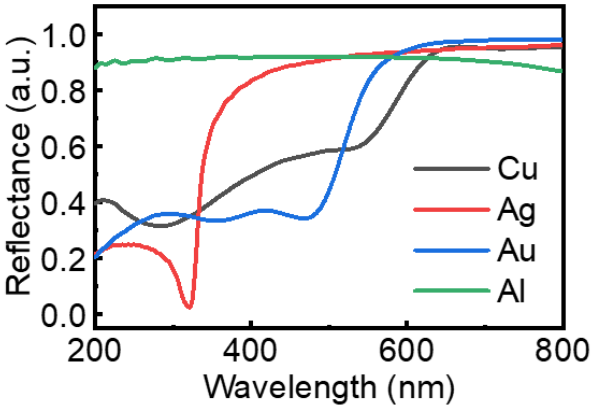


**Fig. S1** Simulated reflectance spectra of different metal films with a thickness of 80 nm.

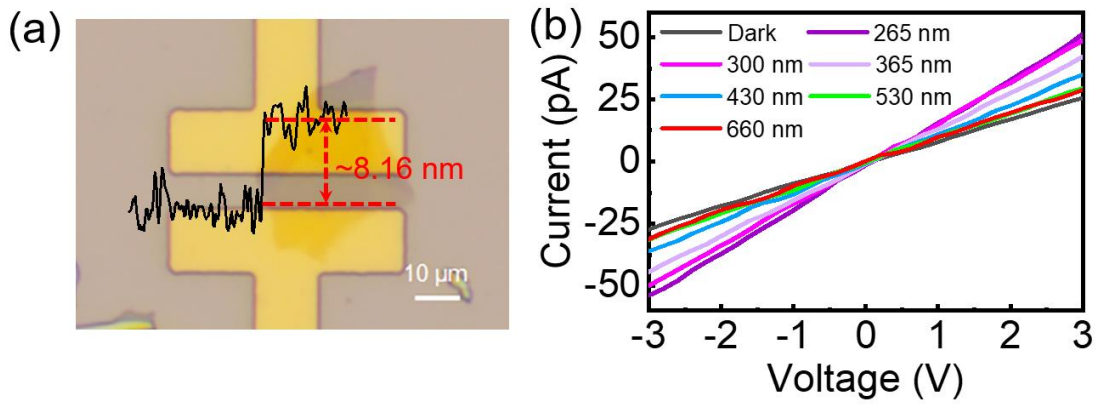


**Fig. S2** (a) Optical microscopy image of a typical GaSe-based photodetector without the asymmetric F-P structure and the height profile of GaSe nanosheet in the channel. (b) *I-V* curves in the dark and upon illumination with varied wavelengths at light intensity of 1 mW/cm$^2$.

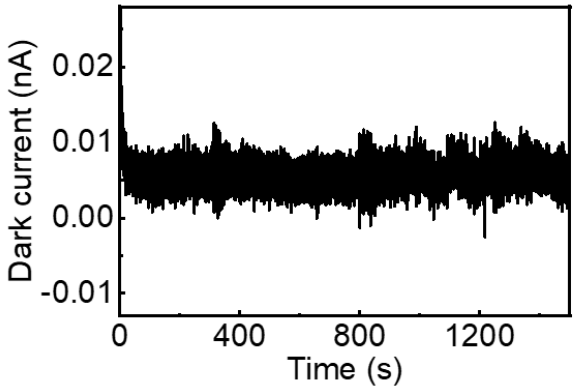


**Fig. S3** Dark current of the device.